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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

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Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100ljafb-30

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

	1	-1	T	(7/12)
Pin count	Package	Data flash	Fields of Application	Ordering Part Number
52 pins	52-pin plastic LQFP (10 × 10	Mounted	A	R5F100JCAFA#V0, R5F100JDAFA#V0, R5F100JEAFA#V0, R5F100JFAFA#V0, R5F100JGAFA#V0, R5F100JHAFA#V0,
	mm, 0.65 mm			R5F100JJAFA#V0, R5F100JKAFA#V0, R5F100JLAFA#V0
	pitch)			R5F100JCAFA#X0, R5F100JDAFA#X0, R5F100JEAFA#X0,
				R5F100JFAFA#X0, R5F100JGAFA#X0, R5F100JHAFA#X0,
				R5F100JJAFA#X0, R5F100JKAFA#X0, R5F100JLAFA#X0
			D	R5F100JCDFA#V0, R5F100JDDFA#V0, R5F100JEDFA#V0,
				R5F100JFDFA#V0, R5F100JGDFA#V0, R5F100JHDFA#V0,
				R5F100JJDFA#V0, R5F100JKDFA#V0, R5F100JLDFA#V0
				R5F100JCDFA#X0, R5F100JDDFA#X0, R5F100JEDFA#X0,
				R5F100JFDFA#X0, R5F100JGDFA#X0, R5F100JHDFA#X0,
				R5F100JJDFA#X0, R5F100JKDFA#X0, R5F100JLDFA#X0
			G	R5F100JCGFA#V0, R5F100JDGFA#V0, R5F100JEGFA#V0,
				R5F100JFGFA#V0,R5F100JGGFA#V0,R5F100JHGFA#V0,
				R5F100JJGFA#V0
				R5F100JCGFA#X0, R5F100JDGFA#X0, R5F100JEGFA#X0,
				R5F100JFGFA#X0,R5F100JGGFA#X0, R5F100JHGFA#X0,
				R5F100JJGFA#X0
		Not	А	R5F101JCAFA#V0, R5F101JDAFA#V0, R5F101JEAFA#V0,
		mounted		R5F101JFAFA#V0, R5F101JGAFA#V0, R5F101JHAFA#V0,
				R5F101JJAFA#V0, R5F101JKAFA#V0, R5F101JLAFA#V0
				R5F101JCAFA#X0, R5F101JDAFA#X0, R5F101JEAFA#X0,
				R5F101JFAFA#X0, R5F101JGAFA#X0, R5F101JHAFA#X0,
				R5F101JJAFA#X0, R5F101JKAFA#X0, R5F101JLAFA#X0
			D	R5F101JCDFA#V0, R5F101JDDFA#V0, R5F101JEDFA#V0,
				R5F101JFDFA#V0, R5F101JGDFA#V0, R5F101JHDFA#V0,
				R5F101JJDFA#V0, R5F101JKDFA#V0, R5F101JLDFA#V0
				R5F101JCDFA#X0, R5F101JDDFA#X0, R5F101JEDFA#X0,
				R5F101JFDFA#X0, R5F101JGDFA#X0, R5F101JHDFA#X0,
				R5F101JJDFA#X0, R5F101JKDFA#X0, R5F101JLDFA#X0

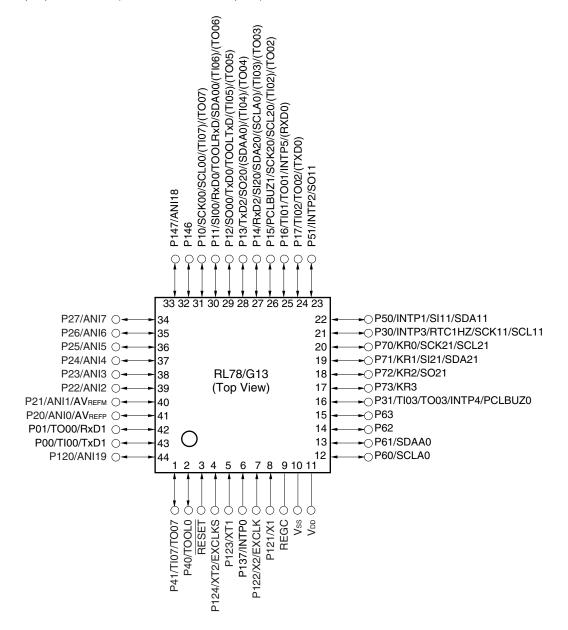
Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3.8 44-pin products

• 44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Юн1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins –170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	Iol1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	IOL2	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins] [5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +85	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Absolute Maximum Ratings (TA = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

$(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1.0		20.0	MHz
frequency (fx) ^{Note}	crystal resonator	$2.4~V \leq V_{\text{DD}} < 2.7~V$	1.0		16.0	MHz
		$1.8~V \leq V_{\text{DD}} < 2.4~V$	1.0		8.0	MHz
		$1.6~V \leq V_{\text{DD}} < 1.8~V$	1.0		4.0	MHz
XT1 clock oscillation frequency (fx) ^{Note}	Crystal resonator		32	32.768	35	kHz

- **Note** Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.
- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to **5.4 System Clock Oscillator**.

2.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Oscillators	Parameters		Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін			1		32	MHz
High-speed on-chip oscillator		–20 to +85 °C	$1.8~V \leq V_{\text{DD}} \leq 5.5~V$	-1.0		+1.0	%
clock frequency accuracy			$1.6~V \leq V_{\text{DD}} < 1.8~V$	-5.0		+5.0	%
		–40 to –20 °C	$1.8~V \leq V_{\text{DD}} \leq 5.5~V$	-1.5		+1.5	%
			$1.6~V \leq V_{\text{DD}} < 1.8~V$	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.



- **Notes 1.** Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz

2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz

LS (low-speed main) mode: $1.8~V \leq V_{\text{DD}} \leq 5.5~V @\,1$ MHz to 8 MHz

LV (low-voltage main) mode: 1.6 V \leq V_DD \leq 5.5 V@1 MHz to 4 MHz

- **Remarks 1.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - **3.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ (1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-	$f_{IH} = 32 \text{ MHz}^{Note 3}$	Basic	$V_{DD} = 5.0 V$		2.3		mA
CURRENT Note 1		mode	speed main) mode ^{Note 5}		operation	$V_{\text{DD}} = 3.0 \text{ V}$		2.3		mA
		mode		Normal	V _{DD} = 5.0 V		5.2	8.5	mA	
				operation	V _{DD} = 3.0 V		5.2	8.5	mA	
			fin = 24 MHz ^{Note 3}	Normal	V _{DD} = 5.0 V		4.1	6.6	mA	
				operation	V _{DD} = 3.0 V		4.1	6.6	mA	
				fin = 16 MHz ^{Note 3}	Normal	V _{DD} = 5.0 V		3.0	4.7	mA
					operation	V _{DD} = 3.0 V		3.0	4.7	mA
			LS (low- speed main) mode ^{Note 5}	f _{IH} = 8 MHz ^{№te 3}	Normal	V _{DD} = 3.0 V		1.3	2.1	mA
					operation	V _{DD} = 2.0 V		1.3	2.1	mA
			LV (low-	$f_{IH}=4\ MHz^{Note3}$	Normal	$V_{DD} = 3.0 V$		1.3	1.8	mA
			voltage main) mode		operation	V _{DD} = 2.0 V		1.3	1.8	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.4	5.5	mA
			speed main) mode ^{Note 5}	V _{DD} = 5.0 V	operation	Resonator connection		3.6	5.7	mA
				$f_{MX} = 20 \text{ MHz}^{Note 2},$	Normal	Square wave input		3.4	5.5	mA
				$V_{DD} = 3.0 V$	operation	Resonator connection		3.6	5.7	mA
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		2.1	3.2	mA
				$V_{DD} = 5.0 V$	operation	Resonator connection		2.1	3.2	mA
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		2.1	3.2	mA
				$V_{DD} = 3.0 V$	operation	Resonator connection		2.1	3.2	mA
			LS (low-	$f_{MX} = 8 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.2	2.0	mA
			speed main) mode ^{Note 5}	$V_{DD} = 3.0 V$	operation	Resonator connection		1.2	2.0	mA
				$f_{MX} = 8 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.2	2.0	mA
				$V_{DD} = 2.0 V$	operation	Resonator connection		1.2	2.0	mA
			Subsystem	fsuв = 32.768 kHz	Normal	Square wave input		4.8	5.9	μA
			clock operation	Note 4 $T_A = -40^{\circ}C$	operation	Resonator connection		4.9	6.0	μA
				fsuв = 32.768 kHz	Normal	Square wave input		4.9	5.9	μA
				Note 4 $T_A = +25^{\circ}C$	operation	Resonator connection		5.0	6.0	μA
				fsuв = 32.768 kHz	Normal	Square wave input		5.0	7.6	μA
				Note 4	operation	Resonator connection		5.1	7.7	μA
				T _A = +50°C fsub = 32.768 kHz	Normal	Square wave input		5.2	9.3	μA
				Note 4	operation	Resonator connection		5.3	9.3 9.4	μA
				$T_A = +70^{\circ}C$	Nama	Company to the state of		F 7	10.0	
				fsub = 32.768 kHz Note 4	Normal operation	Square wave input Resonator connection		5.7 5.8	13.3 13.4	μA μA
				T _A = +85°C	.	TESUTIALUI CUTITIECUUT		5.0	13.4	μΑ

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into Vbb, EVbbb, and EVbb1, including the input leakage current flowing when the level of the input pin is fixed to Vbb, EVbb0, and EVbb1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: 2.7 V \leq V_{DD} \leq 5.5 V@1 MHz to 32 MHz
 - 2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz
 - LS (low-speed main) mode: $~~1.8~V \leq V_{\text{DD}} \leq 5.5~V @\,1~\text{MHz}$ to 8 MHz
 - LV (low-voltage main) mode: 1.6 V \leq V_DD \leq 5.5 V@1 MHz to 4 MHz
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - **3.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



- **Notes 1.** Total current flowing into Vbb, EVbbb, and EVbb1, including the input leakage current flowing when the level of the input pin is fixed to Vbb, EVbb0, and EVbb1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz
 - 2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz
 - LS (low-speed main) mode: $~~1.8~V \leq V_{\text{DD}} \leq 5.5~V~$ @ 1 MHz to 8 MHz
 - LV (low-voltage main) mode: 1.6 V \leq V_{DD} \leq 5.5 V@1 MHz to 4 MHz
 - 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



Parameter	Symbol	Conditions	、 U	h-speed Mode	LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\label{eq:constraint} \begin{array}{l} 2.7~V \leq EV_{\text{DD0}} \leq 5.5~V, \\ C_{\text{b}} = 50~pF,~R_{\text{b}} = 2.7~k\Omega \end{array}$	1/fмск + 85 _{Note2}		1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		ns
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} \leq 5.5 \ V, \\ C_{\text{b}} &= 100 \ p\text{F}, \ R_{\text{b}} = 3 \ k\Omega \end{split}$	1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		ns
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 2.7 \ V, \\ C_{\text{b}} &= 100 \ p\text{F}, \ R_{\text{b}} = 5 \ k\Omega \end{split}$	1/fмск + 230 _{Note2}		1/f _{MCK} + 230 _{Note2}		1/fмск + 230 _{Note2}		ns
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{\tiny DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 \mbox{ k}\Omega \end{array}$	1/fмск + 290 _{Note2}		1/f _{MCK} + 290 _{Note2}		1/fмск + 290 _{Note2}		ns
		$\label{eq:linear} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 k\Omega \end{array}$	—		1/f _{MCK} + 290 _{Note2}		1/fмск + 290 _{Note2}		ns
Data hold time (transmission)	thd:dat	$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	0	305	0	305	0	305	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 3 k\Omega \end{array}$	0	355	0	355	0	355	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 k\Omega \end{array}$	0	405	0	405	0	405	ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$	0	405	0	405	0	405	ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$	_	_	0	405	0	405	ns

(5)	During communication at same potential (simplified I ² C mode) (2/2)
	$(T_{A} = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(**Remarks** are listed on the next page.)



Parameter	Symbol		Conditions		speed	high- main) ode		/-speed Mode	voltage	low- e main) ode	Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Recep- tion	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$			fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 4}$		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate fмск = fclк ^{Note 4}		5.3		1.3		0.6	Mbps
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$			fMCK/6 Notes 1 to 3		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
				Theoretical value of the maximum transfer rate fмск = fclк ^{Note 4}		5.3		1.3		0.6	Mbps

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2) (T_A = -40 to +85°C. 1.8 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V. Vss = EV_{SS0} = EV_{SS1} = 0 V)

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- **2.** Use it with $EV_{DD0} \ge V_b$.
- 3. The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$.

 $2.4~V \leq EV_{\text{DD0}} < 2.7~V$: MAX. 2.6 Mbps

 $1.8~V \leq EV_{\text{DD0}} < 2.4~V$: MAX. 1.3 Mbps

4. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are: HS (high-speed main) mode: $32 \text{ MHz} (2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$

	16 MHz (2.4 V \leq VDD \leq 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq V_{DD} \leq 5.5 V)

LV (low-voltage main) mode: $4 \text{ MHz} (1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$

- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** $V_{b}[V]$: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13)

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.



			$\sqrt{DD0} = EVDD1 \le VDD \le$						11/1	1	Lint
Parameter	Symbol		Conditions			high-		low-		low-	Unit
						main) ode	speed	main) ode		age Mode	
								1			
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$			Note		Note		Note	bps
			$2.7 \text{ V} \leq V_b \leq 4.0 \text{ V}$			1		1		1	
				Theoretical		2.8		2.8		2.8	Mbps
				value of the		Note 2		Note 2		Note 2	
				maximum							
				transfer rate							
				$C_b = 50 \text{ pF}, R_b =$							
				$1.4 \text{ k}\Omega, V_{\text{b}} = 2.7$							
				V							
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$			Note		Note		Note	bps
			$2.3~V \leq V_b \leq 2.7~V$			3		3		3	
				Theoretical		1.2		1.2		1.2	Mbps
				value of the		Note 4		Note 4		Note 4	
				maximum							
				transfer rate							
				$C_b = 50 \text{ pF}, R_b =$							
				$2.7 \text{ k}\Omega$, V _b = 2.3							
				V							
			$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$			Notes		Notes		Notes	bps
			$1.6~V \leq V_b \leq 2.0~V$			5, 6		5, 6		5, 6	
				Theoretical		0.43		0.43		0.43	Mbps
				value of the		Note 7		Note 7		Note 7	
				maximum							
				transfer rate							
				$C_b = 50 \text{ pF}, R_b =$							
				$5.5 \text{ k}\Omega, \text{V}_{\text{b}} = 1.6$							
				V							

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2) (TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Notes 1. The smaller maximum transfer rate derived by using fMck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV $_{DD0} \leq$ 5.5 V and 2.7 V \leq V $_{b} \leq$ 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

Parameter	Symbol		Conditions	HS (hig	h-speed Mode	LS (low		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү1	tксү1 ≥ 4/fc∟к	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$	300		1150		1150		ns
			$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	500		1150		1150		ns
			$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note}}, \end{array}$	1150		1150		1150		ns
SCKp high-level width	tкнı	$4.0 \text{ V} \leq \text{EV}_{\text{DI}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq$	4.0 V,	tксү1/2 – 75		tксү1/2 – 75		tксү1/2 – 75		ns
		$C_b = 30 \text{ pF},$ 2.7 V $\leq EV_{DI}$ 2.3 V $\leq V_b \leq$ $C_b = 30 \text{ pF},$	₂₀ < 4.0 V, 2.7 V,	tксү1/2 – 170		tксү1/2 – 170		tксү1/2 – 170		ns
		$1.8 V \le EV_{DI}$ $1.6 V \le V_b \le C_b = 30 \text{ pF},$	2.0 V ^{Note} ,	tксү1/2 – 458		tксү1/2 – 458		tксү1/2 – 458		ns
SCKp low-level width	tĸ∟ı	$4.0 \text{ V} \leq \text{EV}_{\text{DI}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 30 \text{ pF},$	∞ ≤ 5.5 V, 4.0 V,	tксү1/2 – 12		tксү1/2 – 50		tксү1/2 – 50		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DI} \\ 2.3 \ V \leq V_b \leq \end{array}$	₀₀ < 4.0 V, 2.7 V,	tксү1/2 – 18		tксү1/2 – 50		tксү1/2 – 50		ns
		$\label{eq:cb} \begin{array}{l} C_{\rm b} = 30 \mbox{ pF}, \\ \\ 1.8 \mbox{ V} \leq EV_{\rm DI} \\ 1.6 \mbox{ V} \leq V_{\rm b} \leq \\ \\ C_{\rm b} = 30 \mbox{ pF}, \end{array}$	⁰⁰ < 3.3 V, 2.0 V ^{Note} ,	tксү1/2 – 50		tксү1/2 – 50		tксү1/2 – 50		ns

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Note Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)



(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter Symb			<u>< VDD < 5.5 V, Vss =</u> nditions		high- main)	LS (low	S (low-speed LV (low-voltage main) Mode main) Mode			Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time ^{Note 1}		$4.0 V \le EV_{DD0} \le 5.5 V$, $2.7 V \le V_b \le 4.0 V$	24 MHz < fмск	14/ fмск		_		_		ns
			20 MHz < fмск ≤ 24 MHz	12/ fмск		_		_		ns
			8 MHz < fмск ≤ 20 MHz	10/ fмск						ns
			4 MHz < fмск ≤ 8 MHz	8/fмск		16/ fмск				ns
			fмск ≤4 MHz	6/fмск		10/ fмск		10/ fмск		ns
		$2.7 V \le EV_{DD0} < 4.0 V,$ $2.3 V \le V_b \le 2.7 V$	24 MHz < fмск	20/ fмск						ns
			20 MHz < fмск ≤ 24 MHz	16/ fмск				—		ns
			16 MHz < fмск ≤ 20 MHz	14/ fмск						ns
			8 MHz < fмск ≤ 16 MHz	12/ fмск		—				ns
			4 MHz < fмск ≤ 8 MHz	8/fмск		16/ fмск				ns
			fмск ≤4 MHz	6/fмск		10/ fмск		10/ fмск		ns
		$\begin{split} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note}} \end{split}$	24 MHz < fмск	48/ fмск		—		—		ns
		2	20 MHz < fмск ≤ 24 MHz	36/ fмск		—		—		ns
			16 MHz < fмск ≤ 20 MHz	32/ fмск		—		_		ns
			8 MHz < fмск ≤ 16 MHz	26/ fмск		—		_		ns
			4 MHz < fмск ≤ 8 MHz	16/ fмск		16/ fмск		—		ns
			fмск ≤4 MHz	10/ fмск		10/ fмск		10/ fмск		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)



(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Conditions	HS (speed	high-	LS (low	· · ·	•	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	tкн2, tкL2	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$	tксү2/2 – 12		tксү2/2 - 50		tксү2/2 - 50		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$	tксү2/2 – 18		tксү2/2 - 50		tксү2/2 - 50		ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{array}$	tксү2/2 - 50		tксү2/2 - 50		tксү2/2 - 50		ns
SIp setup time (to SCKp↑) ^{Note 3}	tsiк2	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$\begin{array}{l} 2.7 \ V \leq E V_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{array}$	1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
SIp hold time (from SCKp↑) ^{Note 4}	tksı2		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp output Note 5	tĸso2	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \\ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$		2/fмск + 120		2/fмск + 573		2/fмск + 573	ns
		$\label{eq:V} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \\ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		2/fмск + 214		2/fмск + 573		2/fмск + 573	ns
		$\begin{split} 1.8 \ V &\leq E V_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note } 2}, \\ C_b &= 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

- **2.** Use it with $EV_{DD0} \ge V_b$.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)



3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (1/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{∾te 1}	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$2.4~V \leq EV_{DD0} \leq 5.5~V$			-3.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$			-30.0	mA
		P125 to P127, P130, P140 to P145	$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-10.0	mA
			$2.4~V \leq EV_{\text{DD0}} < 2.7~V$			-5.0	mA
		Total of P05, P06, P10 to P17, P30, P31,		-30.0	mA		
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty $\leq 70\%$ ^{Note 3})	$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-19.0	mA
			$2.4~V \leq EV_{DD0} < 2.7~V$			-10.0	mA
		Total of all pins (When duty ≤ 70% ^{№te 3})	$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V$			-60.0	mA
	Іон2	Per pin for P20 to P27, P150 to P156	2,4 V \leq V_{DD} \leq 5.5 V			-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%^{Note 3}$)	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.
 - 2. Do not exceed the total current value.
 - 3. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).
 - Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 80% and $I_{OH} = -10.0 \text{ mA}$
 - Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -3.0 \ mA \end{array}$	EV _{DD0} - 0.7			V
		P90 to P97, P100 to P106, P110 to lo	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Ioh1 = -2.0 mA	EV _{DD0} - 0.6			V
	Р140 to P147 Іон1 = -1.5 mA	EV _{DD0} - 0.5			V		
Voh2	Vон2	P20 to P27, P150 to P156	2.4 V \leq V _{DD} \leq 5.5 V, Іон ₂ = -100 μ А	Vdd - 0.5			V
low	Vol1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 8.5 \ mA \end{array} \end{array} \label{eq:eq:optimal_decay}$			0.7	V
		P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 3.0 \ mA \end{array} \end{array} \label{eq:DD1}$			0.6	V
			$eq:local_$			0.4	V
			$eq:local_$			0.4	V
	Vol2	P20 to P27, P150 to P156	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $\text{Iol2} = 400 \ \mu \text{ A}$			0.4	V
	Vol3		$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ I_{\text{OL3}} = 15.0 \ mA \end{array}$			2.0	V
		$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ \\ I_{\text{OL3}} = 5.0 \ mA \end{array}$			0.4	V	
		$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ I_{\text{OL3}} = 3.0 \ mA \end{array}$			0.4	V	
			$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $I_{\text{OL3}} = 2.0 \text{ mA}$			0.4	V

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (4/5)

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (1/2) (T_A = -40 to +105°C, 2.4 V \leq EVpp0 = EVpp1 \leq Vpp \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions		peed main) ode	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{split} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$		400 ^{Note 1}	kHz
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 50 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$		400 ^{Note 1}	kHz
				100 ^{Note 1}	kHz
		$\label{eq:2.7} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$		100 ^{Note 1}	kHz
		$\label{eq:2.4} \begin{split} 2.4 \ V &\leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V, \\ C_b &= 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$		100 ^{Note 1}	kHz
Hold time when SCLr = "L"	t∟ow	$ \begin{split} & 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ & 2.7 \; V \leq V_b \leq 4.0 \; V, \\ & C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{split} $	1200		ns
		$\label{eq:2.7} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	1200		ns
		$\label{eq:loss} \begin{split} & 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ & 2.7 \ V \leq V_b \leq 4.0 \ V, \\ & C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{split}$	4600		ns
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	4600		ns
		$\label{eq:2.4} \begin{split} & 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	4650		ns
Hold time when SCLr = "H"	tніgн		620		ns
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 50 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$	500		ns
		$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{array}$	2700		ns
		$\label{eq:2.7} \begin{split} & 2.7 \; V \leq EV_{\text{DD0}} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	2400		ns
		$\label{eq:2.4} \begin{split} & 2.4 \; V \leq EV_{\text{DD0}} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	1830		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)



4.9 48-pin Products

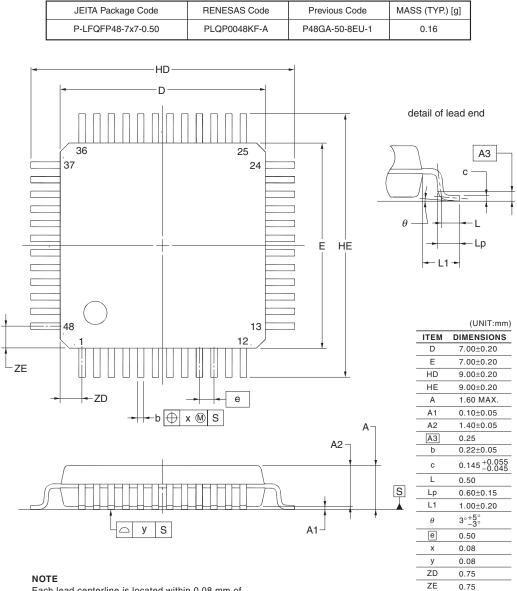
R5F100GAAFB, R5F100GCAFB, R5F100GDAFB, R5F100GEAFB, R5F100GFAFB, R5F100GGAFB, R5F100GHAFB, R5F100GJAFB, R5F100GKAFB, R5F100GLAFB

R5F101GAAFB, R5F101GCAFB, R5F101GDAFB, R5F101GEAFB, R5F101GFAFB, R5F101GGAFB, R5F101GHAFB, R5F101GJAFB, R5F101GKAFB, R5F101GLAFB

R5F100GADFB, R5F100GCDFB, R5F100GDDFB, R5F100GEDFB, R5F100GFDFB, R5F100GGDFB, R5F100GHDFB, R5F100GJDFB, R5F100GKDFB, R5F100GLDFB

R5F101GADFB, R5F101GCDFB, R5F101GDDFB, R5F101GEDFB, R5F101GFDFB, R5F101GGDFB, R5F101GHDFB, R5F101GJDFB, R5F101GKDFB, R5F101GLDFB

R5F100GAGFB, R5F100GCGFB, R5F100GDGFB, R5F100GEGFB, R5F100GFGFB, R5F100GGGFB, R5F100GHGFB, R5F100GJGFB



Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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R5F100LCAFB, R5F100LDAFB, R5F100LEAFB, R5F100LFAFB, R5F100LGAFB, R5F100LHAFB, R5F100LJAFB, R5F100LLAFB

R5F101LCAFB, R5F101LDAFB, R5F101LEAFB, R5F101LFAFB, R5F101LGAFB, R5F101LHAFB,

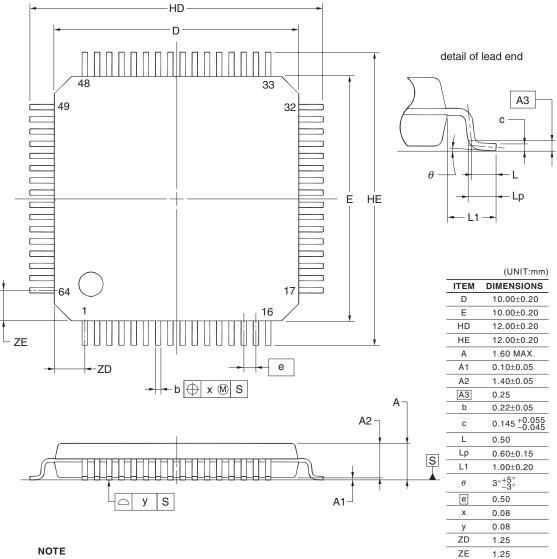
R5F101LJAFB, R5F101LKAFB, R5F101LLAFB

R5F100LCDFB, R5F100LDDFB, R5F100LEDFB, R5F100LFDFB, R5F100LGDFB, R5F100LHDFB, R5F100LJDFB, R5F100LLDFB

R5F101LCDFB, R5F101LDDFB, R5F101LEDFB, R5F101LFDFB, R5F101LGDFB, R5F101LHDFB, R5F101LJDFB, R5F101LKDFB, R5F101LLDFB

R5F100LCGFB, R5F100LDGFB, R5F100LEGFB, R5F100LFGFB, R5F100LGGFB, R5F100LHGFB, R5F100LJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP64-10x10-0.50	PLQP0064KF-A	P64GB-50-UEU-2	0.35



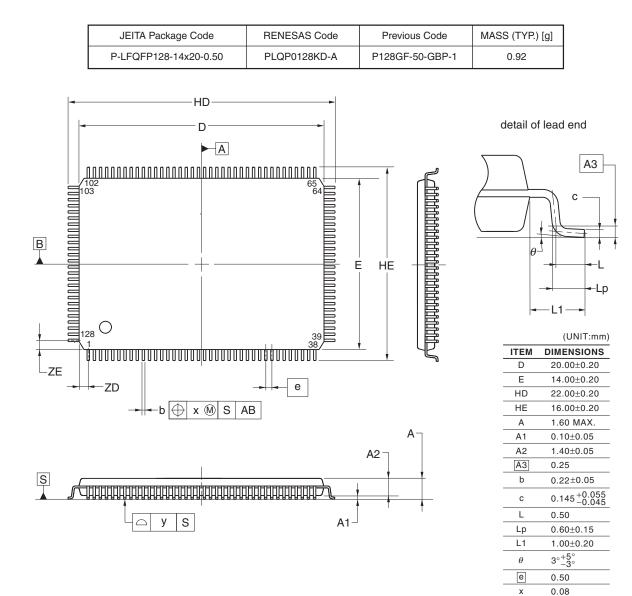
Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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4.14 128-pin Products

R5F100SHAFB, R5F100SJAFB, R5F100SKAFB, R5F100SLAFB R5F101SHAFB, R5F101SJAFB, R5F101SKAFB, R5F101SLAFB R5F100SHDFB, R5F100SJDFB, R5F100SKDFB, R5F100SLDFB R5F101SHDFB, R5F101SJDFB, R5F101SKDFB, R5F101SLDFB



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0.75

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